ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE601
Silicon Varistor
Temperature Compensating Diode

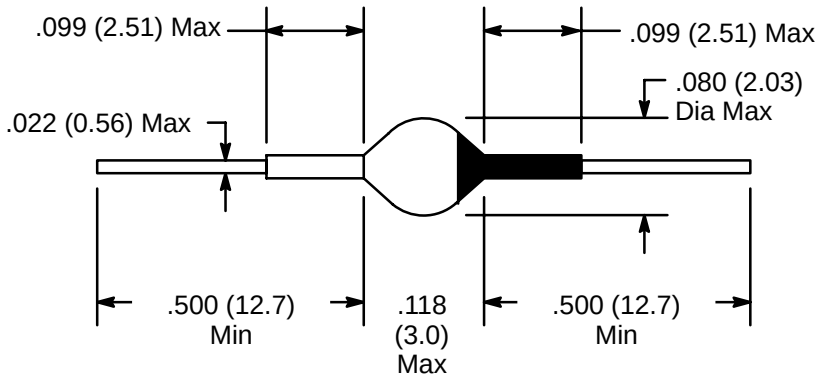
Features:
- High reliability planar chip and glass sealing
- Low I_R
- Large P_D

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Maximum Forward Current, I_{FM} 150mA
Reverse Voltage, V_R 6V
Power Dissipation, P_D 150mW
Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Current	I_R	V_R = 6V	–	–	10	μA
Forward Voltage	V_F	I_F = 1.5mA	0.59	–	0.64	V
		I_F = 50mA	–	–	1.1	V
Forward Voltage Change with Respect to Temperature	$-\Delta V_F/\Delta T$	I_F = 1.5mA	–	2.0	–	mV/°C



Color Band Denotes Cathode